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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **NISHIUCHI, et al.**

Group Art Unit: 1763

Serial No.: 10/615,381

Examiner: **Richard R. BUEKER**

Filed: **July 9, 2003**

P.T.O. Confirmation No.: 1378

For. **SURFACE TREATING APPARATUS (AS AMENDED)**

**INFORMATION DISCLOSURE STATEMENT AND STATEMENT
PURSUANT TO 37 CFR 1.97(d)**

Attn: Group Director

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

August 2, 2007

Sir:

The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached Form PTO-1449. A copy of each non-U.S. Patent document is attached.

This Information Disclosure Statement is submitted after the mailing of a final action, a Notice of Allowance, or an action that otherwise closes prosecution in the application, but on or before payment of the Issue Fee.

The undersigned hereby certifies:

XX That each item of information contained in this Information Disclosure Statement was first cited in a communication from the European Patent Office in a counterpart application on June 4, 2007, not more than three months prior to the filing of this Information Disclosure Statement;

08/03/2007 HLE333 00000075 012340 10615381

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Information Disclosure Statement Under 37 CFR 1.97(d)
U.S. Patent Application Serial No. 10/615,381

____ That no item of information contained in this statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned after making reasonable inquiry, no information contained in this statement was known to any individual designated in 37 CFR § 1.56(c) more than three months prior to the filing of this statement.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.

Please charge the \$180.00 fee required under 37 CFR § 1.17(p) to Deposit Account No. 01-2340.

Respectfully submitted,

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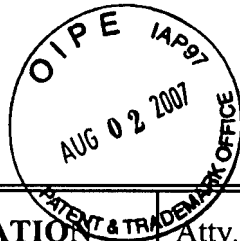
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PATENT TRADEMARK OFFICE

Enclosures: PTO 1449; Copy of ESR dated June 4, 2007; References (9)



INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 000593B	Serial No. 10/615,381
	Applicant(s): NISHIUCHI, et al.	
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U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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_____	AI			
_____	AJ			

Examiner	Date Considered
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OTHER DOCUMENTS

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Examiner _____ Date Considered _____		